

## OPE5194WK

The **OPE5194WK** is GaAlAs infrared emitting diode that is designed for high radiant intensity and low forward voltage. This device is optimized for efficiency at emission wavelength 940nm and has a high radiant efficiency over a wide range of forward current. This device is packaged T1-3/4 plastic package and has narrow beam angle with lensed package and cup frame.

### FEATURES

- High-output power
- Narrow beam angle
- Available for pulse operating

### APPLICATIONS

- Optical emitters
- Optical switches
- Smoke sensors
- IR remote control
- IR sound transmission

### STORAGE

- Condition : 5°C~35°C, R.H.60%
- Terms : within 3 months from production date
- Remark : Once the package is opened, the products should be used within a day.  
Otherwise, it should be keeping in a damp proof box with desiccants.

\* Please take proper steps in order to secure reliability and safety in required conditions and environments for this device.

### MAXIMUM RATINGS

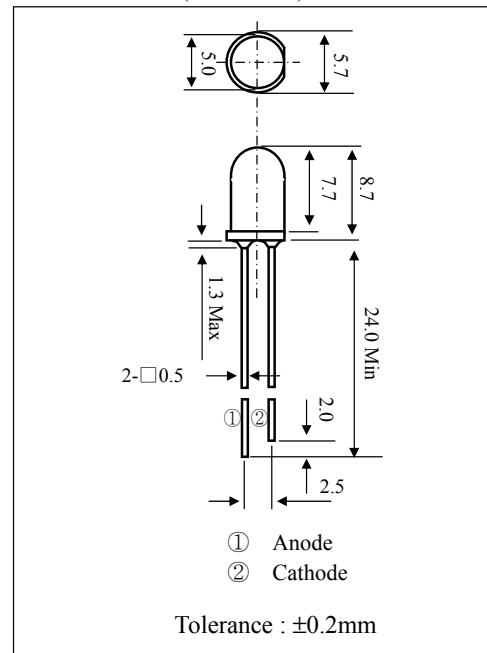
(Ta=25°C)

| Item                                | Symbol            | Rating  | Unit |
|-------------------------------------|-------------------|---------|------|
| Power Dissipation                   | P <sub>D</sub>    | 150     | mW   |
| Forward current                     | I <sub>F</sub>    | 100     | mA   |
| Pulse forward current <sup>*1</sup> | I <sub>FP</sub>   | 1.0     | A    |
| Reverse voltage                     | V <sub>R</sub>    | 5.0     | V    |
| Operating temp.                     | To pr.            | -25~+85 | °C   |
| Soldering temp. <sup>*2</sup>       | T <sub>sol.</sub> | 260.    | °C   |

<sup>\*1</sup>. Duty ratio = 1/100, pulse width=0.1ms.

<sup>\*2</sup>. Lead Soldering Temperature (2mm from case for 5sec.).

### DIMENSIONS (Unit : mm)



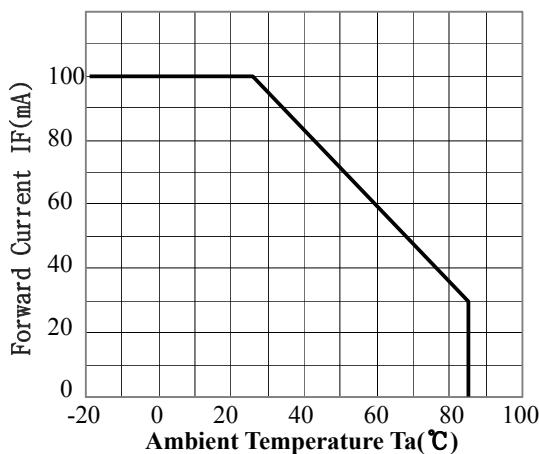
Tolerance : ±0.2mm

### ELECTRO-OPTICAL CHARACTERISTICS

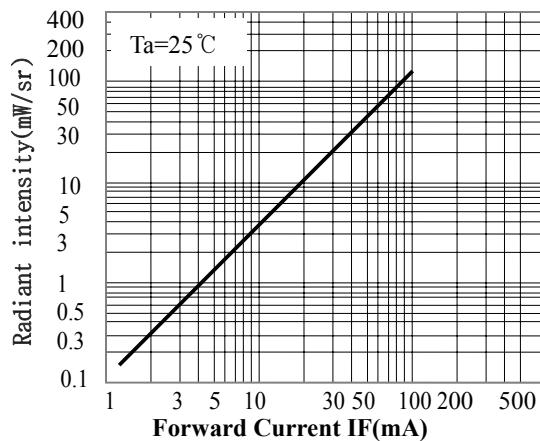
(Ta=25°C)

| Item                     | Symbol         | Conditions            | Min. | Typ. | Max. | Unit  |
|--------------------------|----------------|-----------------------|------|------|------|-------|
| Forward voltage          | V <sub>F</sub> | I <sub>F</sub> =100mA |      | 1.4  | 1.7  | V     |
| Reverse current          | I <sub>R</sub> | V <sub>R</sub> = 5V   |      |      | 10   | μA    |
| Capacitance              | C <sub>t</sub> | f = 1MHz              |      | 20   |      | pF    |
| Radiant intensity        | I <sub>e</sub> | I <sub>F</sub> =100mA |      | 120  |      | mW/sr |
| Peak emission wavelength | λ <sub>p</sub> | I <sub>F</sub> = 50mA |      | 940  |      | nm    |
| Spectral bandwidth 50%   | Δ λ            | I <sub>F</sub> = 50mA |      | 45   |      | nm    |
| Half angle               | Δ Θ            | I <sub>F</sub> =100mA |      | ±10  |      | deg.  |

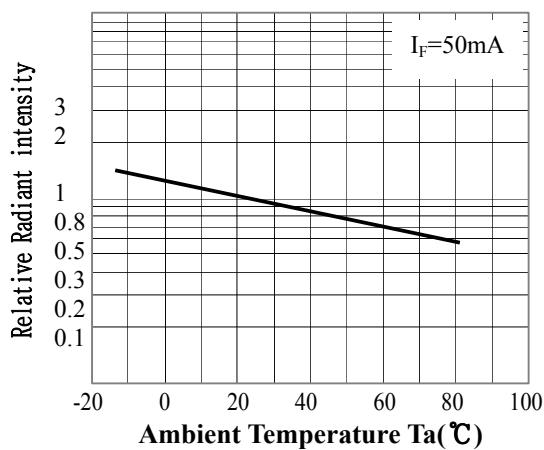
- FORWARD CURRENT Vs. AMBIENT TEMP.



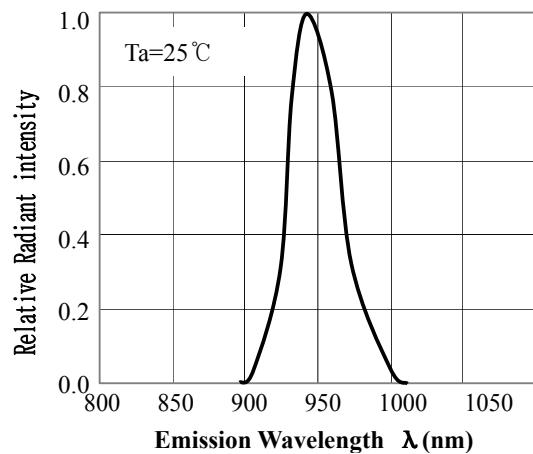
- RADIANT INTENSITY Vs. FORWARD CURRENT.



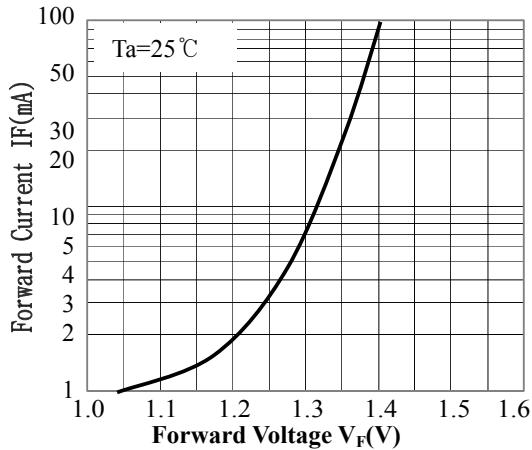
- RELATIVE RADIANT INTENSITY Vs. AMBIENT TEMP.



- RELATIVE RADIANT INTENSITY Vs. EMISSION WAVELENGTH.



- FORWARD CURRENT Vs. FORWARD VOLTAGE



- ANGULAR DISPLACEMENT Vs. RELATIVE RADIANT INTENSITY

